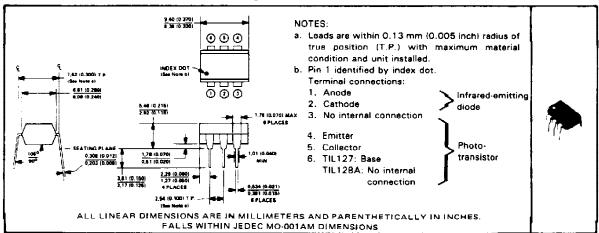
- Gallium Arsenida Diode Infrared Source Optically Coupled to a Silicon N-P-N Darlington-Connected Phototransistor
- High Direct-Current Transfer Ratio . . . 300% Minimum at 10 mA
- High-Voltage Electrical Isolation . . . 5000-Volt Rating
- Plastic Dual-In-Line Package
- Typical Applications Include Remote Terminal Isolation, SCR and Triac Triggers, Mechanical Relays, and Pulse Transformers
- No Base Connection on TIL128A for Environments with High Electromagnetic Interference

#### mechanical data

The package consists of a gallium arsenide infrared-emitting diode and an n-p-n silicon phototransistor mounted on a 6-lead frame encapsulated within an electrically nonconductive plastic compound. The case will withstand soldering temperature with no deformation, and device performance characteristics remain stable when operated in high-humidity conditions. Unit weight is approximately 0.52 grams.



#### absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Input-to-Output Voltage	k٧
Collector-Base Voltage (TIL127)	V
Collector-Emitter Voltage (See Note 1)	) V
Emitter-Collector Voltage	V
Emitter-Base Voltage (TIL127)	7 V
Input Diode Reverse Voltage	3 V
Input-Diode Continuous Forward Current	nΑ
Continuous Power Dissipation at (or below) 25°C Free-Air Temperature:	
Infrared-Emitting Diode (See Note 2)	n₩
Phototransistor (See Note 3)	n₩
Total (Infrared-Emitting Diode plus Phototransistor, See Note 4)	nΨ
Storage Temperature Range	)°C
Lead Temperature 1,6 mm (1/16 Inch) from Case for 10 Seconds	

NOTES: 1. This value applies when the base-emitter diode is open-circuited.

- 2. Derate linearly to 100°C free-air temperature at the rate of 2 mW/°C.
- 3. Derate linearly to 100°C free-air temperature at the rate of 2 mW/°C.
- 4. Denate linearly to 100°C free-air temperature at the rate of 3.33 mW/°C.

PRODUCTION DATA documents contain information current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all perameters.

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# TIL127, TIL128A OPTOCOUPLERS

## electrical characteristics at 25°C free-air temperature

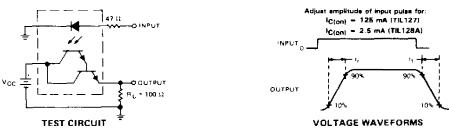
PARAMETER		TEST CONDITIONST			TIL127			1	UNIT			
					MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
V(BR)CBO	Collector-Base Breakdown Voltage	I <sub>C</sub> = 10 μA,	IE = 0,	le = 0	30						٧	
V(BRICEO	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1 mA,	IB = 0.	1F - 0	30			30			٧	
Vівятево	Emitter-Base Breakdown Voltage	IE = 10 μA,	IC = 0'	1 <sub>F</sub> = 0	7						>	
V(BR)ECO	Emitter-Collector Breakdown Voltage	IE = 10 μA,	1F = 0					7			٧	
I <sub>R</sub>	Input Diode Static Reverse Current	V <sub>H</sub> = 3 V					10			10	μА	
(Clan)	On-State	VCE = 1 V,	1B = 0'	Ip = 10 mA	30	100				10	mΑ	
	Callector Current	VCE = I V.	IF = 10 mA					30	160		\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
IC(off)	Off-State Collector Current	V <sub>CE</sub> = 10 V,	I <sub>B</sub> = 0,	I <sub>F</sub> = 0			100		·	100	n <b>A</b>	
hFE	Transistor Static Forward Current Transfer Ratio	V <sub>CE</sub> = 1 V,	I <sub>C</sub> 10 mA,	1 <sub>F</sub> = 0		5 000						
٧ <sub>E</sub>	Input Diode Static Forward Voltage	I <sub>F</sub> = 10 mA					1.5			1.5	v	
	Collector-Emitter	I <sub>C</sub> 125 mA,	IB = 0,	1 <sub>F</sub> = 50 mA			1.2	1			V	
VCE(sat)	Saturation Voltage	IC = 30 mA	I <sub>F</sub> = 10 mA							1	"	
rio	Input-to-Output Internal Resistance	V <sub>in-out</sub> = 500 V,	See Note 5		1011			1011			Ω	
C <sub>io</sub>	Input-to-Output Capacitance	Vin-out = 0,	f = 1 MHz,	See Note 5		1	1,3		1	1.3	рF	

NOTE 5: These parameters are measured between both input-diode leads shorted together and all the phototransistor leads shorted together.  $^{\dagger}$ References to the base are not applicable to the TIL128A.

# switching characteristics at 25°C free-air temperature

PARAMETER		TER	TEST CONDITIONS†		TIL127			TIL128A			
PARAMETER	163	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT		
tr	Rise Time	V <sub>CC</sub> = 15 V,	I <sub>C(оп)</sub> = 125 mA,		300						
tf	Fall Time	R <sub>L</sub> = 100 Ω,	See Figure 1		300					дз	
t <sub>r</sub>	Rise Time	V <sub>CC</sub> = 10 V,	I <sub>C(on)</sub> = 2.5 mA,					300		_	
tf	Fall Time	R <sub>L</sub> = 100 Ω,	See Figure 1				T -	300		μ5	

## PARAMETER MEASUREMENT INFORMATION



- NOTES: a. The input waveform is supplied by a generator with the following characteristics:  $Z_{out}$  = 50  $\Omega$ ,  $\tau_r \le$  15 ns, duty cycle  $\approx$  1%, t  $_{\rm W}$  = 500  $\mu$ s. b. The output waveform is monitored on an oscilloscope with the following characteristics:  $t_{\rm f}$   $\leq$  12 ns,  $R_{\rm HI}$  > 1 M $\Omega$ ,  $C_{\rm HI}$   $\leq$  20 pF

# FIGURE 1-SWITCHING TIMES

#### TYPICAL CHARACTERISTICS

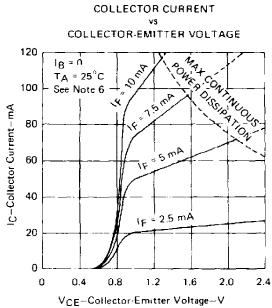


FIGURE 2

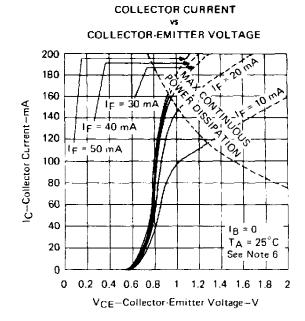
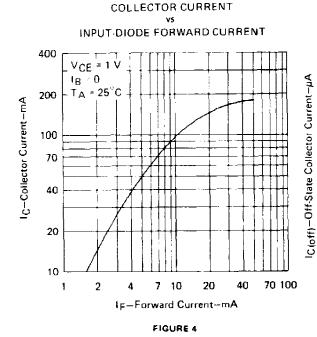


FIGURE 3



OFF-STATE COLLECTOR CURRENT

VS

FREE-AIR TEMPERATURE

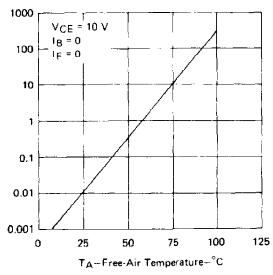


FIGURE 5

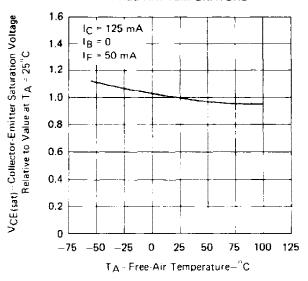
NOTE 6: Pulse operation of input diode is required for operation beyond limits shown by dotted line.



### TYPICAL CHARACTERISTICS

# RELATIVE COLLECTOR-EMITTER SATURATION VOLTAGE VS

FREE-AIR TEMPERATURE



# TIL127 TRANSISTOR STATIC FORWARD CURRENT TRANSFER RATIO vs

COLLECTOR CURRENT

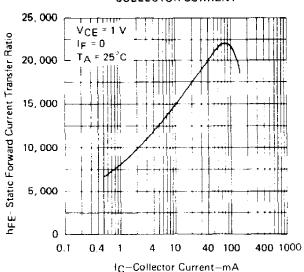
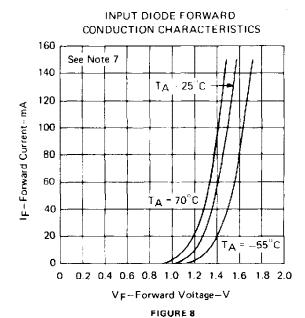


FIGURE 6

FIGURE 7



NOTE 7: This parameter was measured using pulse techniques,  $t_{\rm w}$  = 1 ms, duty cycle  $\leq -2\%$ .



4

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